

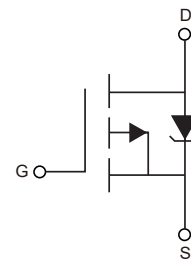
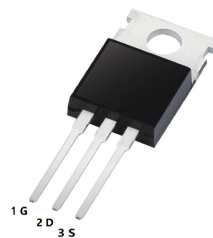
1. Description

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts.

3. Pinning information

Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE

TO-220



4. Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Continuous Drain Current, $V_{GS}=-10V$	$T_C=25^{\circ}C$	I_D	-19	A
Continuous Drain Current, $V_{GS}=-10V$	$T_C=100^{\circ}C$		-14	A
Pulsed Drain Current ①		I_{DM}	-68	A
Power Dissipation	$T_C=25^{\circ}C$	P_D	68	W
Linear Derating Factor			0.45	W/ $^{\circ}C$
Gate-to-Source Voltage		V_{GS}	± 20	V
Single Pulse Avalanche Energy②		E_{AS}	180	mJ
Avalanche Current①		I_{AR}	-10	A
Repetitive Avalanche Energy①		E_{AR}	6.8	mJ
Peak Diode Recovery dv/dt ③		dv/dt	-5	V/ns
Storage Temperature Range		T_J, T_{STG}	-55 to 175	$^{\circ}C$
Soldering Temperature, for 10 seconds			300 (1.6mm from case)	$^{\circ}C$
Mounting torque, 6-32 or M3 screw			10 lbf•in (1.1N•m)	



5.Thermal resistance rating

Parameter	Symbol	Typ	Max	Units
Junction-to-Case	$R_{\theta JC}$		2.2	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{\theta CS}$	0.5		°C/W
Junction-to-Ambient	$R_{\theta JA}$		62	°C/W



6. Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -250\mu\text{A}$, $V_{GS} = 0\text{V}$	-55			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/T_J$	$I_D = -1\text{mA}$, Reference to 25°C		-0.05		V/ $^\circ\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10\text{V}$, $I_D = -10\text{A}$ ④			100	m Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\mu\text{A}$	-2		-4	V
Forward Transconductance	g_{FS}	$V_{DS} = 25\text{V}$, $I_D = -10\text{A}$	4.2			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -55\text{V}$, $V_{GS} = 0\text{V}$			-25	μA
		$V_{DS} = -44\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 150^\circ\text{C}$			-250	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = 20\text{V}$			100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = -20\text{V}$			-100	nA
Total Gate Charge	Q_g	$I_D = -10\text{A}$			35	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -44\text{V}$, $V_{GS} = -10\text{V}$			7.9	nC
Gate-to-Drain ("Miller") Charge	Q_{gd}	See Fig. 6 and 13 ④			16	nC
Turn-On Delay Time	$t_{D(on)}$	$V_{DD} = -28\text{V}$, $I_D = -10\text{A}$ $R_G = 13\Omega$, $R_D = 2.6\Omega$ See Fig. 10 ④		13		ns
Rise Time	t_r			55		ns
Turn-Off Delay Time	$t_{D(off)}$			30		ns
Fall Time	t_f			41		ns
Internal Drain inductance	L_D	Between lead, 6mm (0.25in.) from package and center of die contact		4.5		nH
Internal Source inductance	L_S			7.5		nH
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$ $f = 1.0\text{MHz}$, See Fig. 5		620		pF
Output Capacitance	C_{oss}			280		pF
Reverse Transfer Capacitance	C_{rss}			140		pF



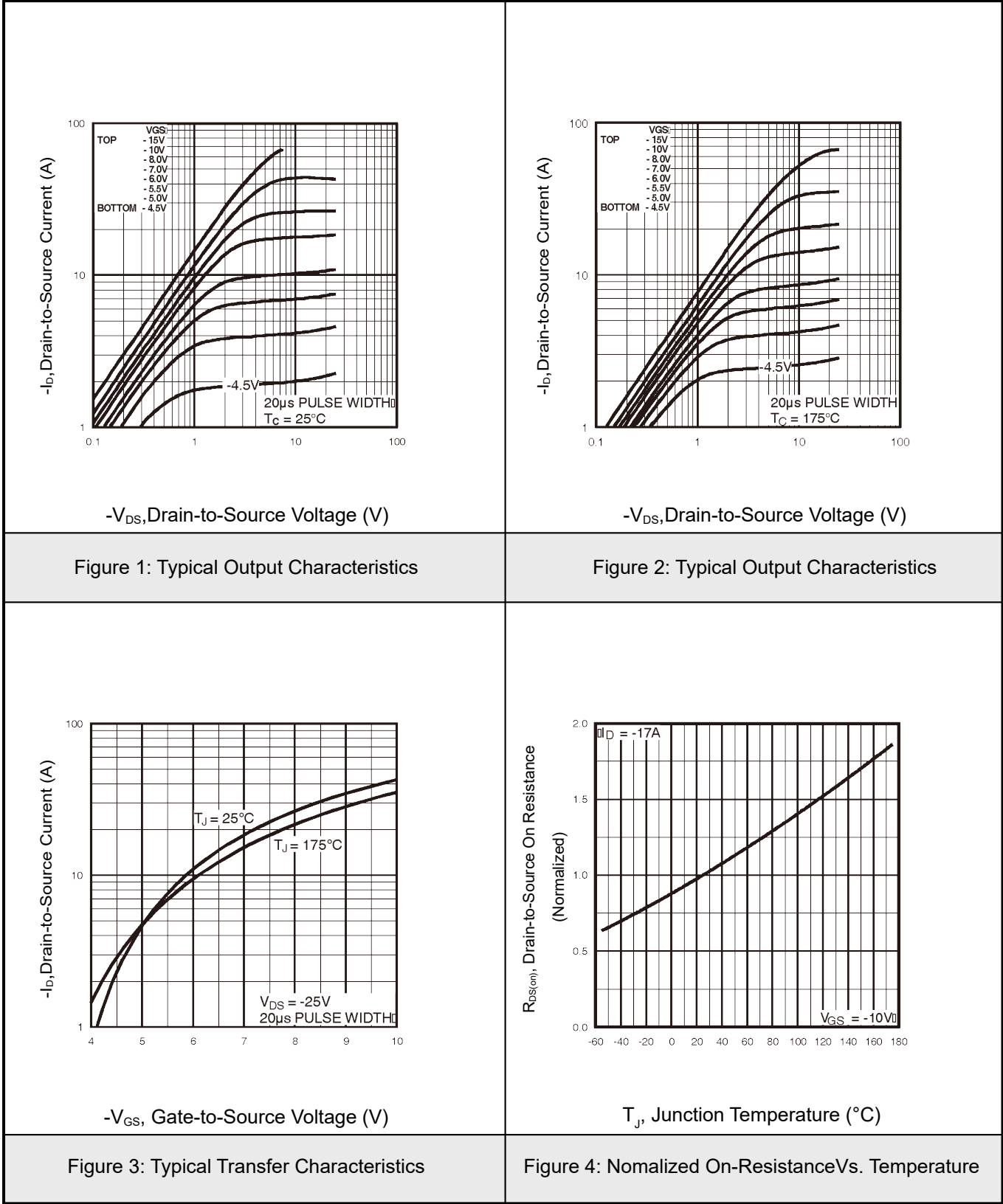
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.			-19	A
Pulsed Source Current (Body Diode) ①	I_{SM}				-68	
Diode Forward Voltage	V_{SD}	$T_J=25^{\circ}\text{C}$, $I_S=-10\text{A}$, $V_{GS}=0\text{V}$ ④			-1.6	V
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}\text{C}$, $I_F=-10\text{A}$ $di/dt=-100\text{A}/\mu\text{s}$ ④		54	82	ns
Reverse Recovery Charge	Q_{rr}			110	160	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J=25^{\circ}\text{C}$, $L=3.6\text{mH}$, $R_G=25\Omega$, $I_{AS}=-10\text{A}$.
- ③ $I_{SD}\leq-10\text{A}$, $di/dt\leq-290\text{A}/\mu\text{s}$, $V_{DD}\leq V_{(BR)DSS}$, $T_J\leq175^{\circ}\text{C}$.
- ④ Pulse width $\leq300\mu\text{s}$; duty cycle $\leq2\%$.

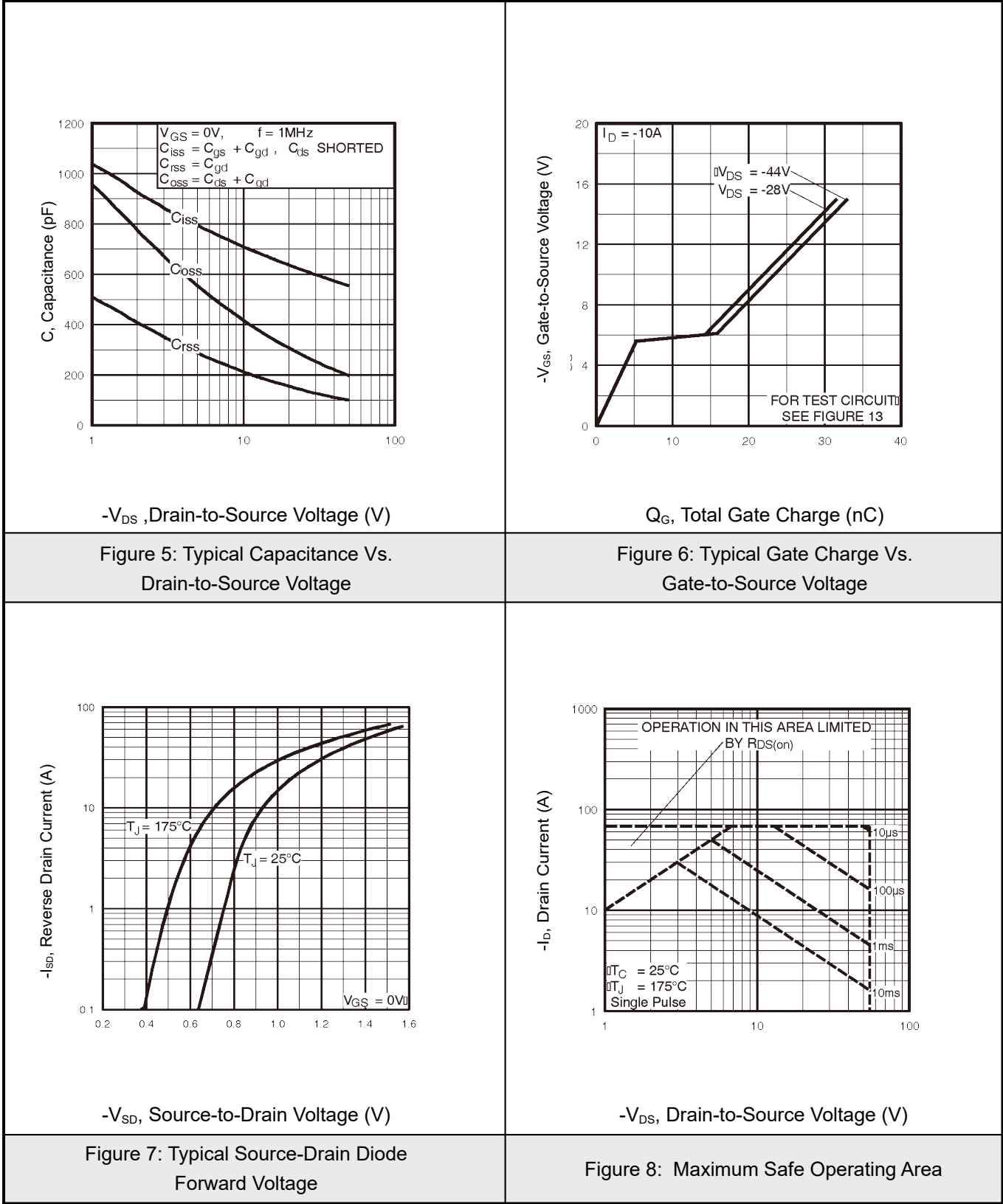


7.1 Typical Characteristics



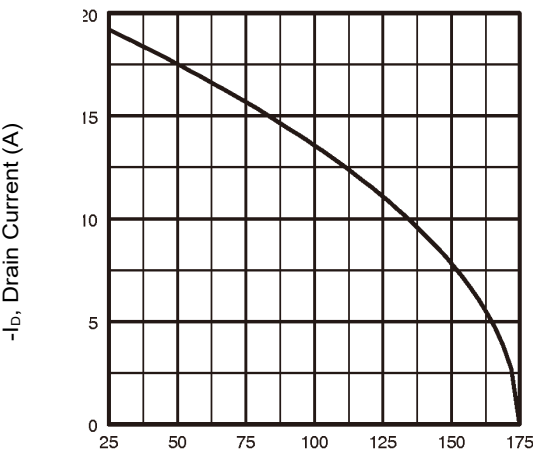


7.2 Typical Characteristics



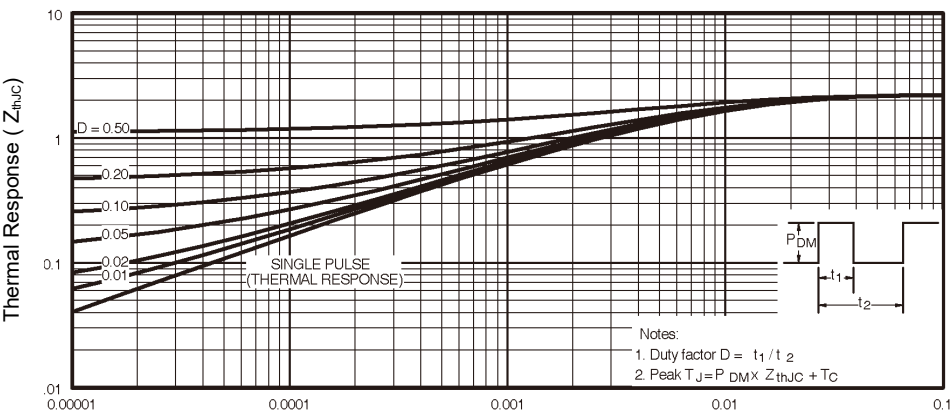


7.3Typical Characteristics



T_c, Case Temperature (C)

Figure 9: Maximum Drain Current Vs. Case Temperature



t₁ , Rectangular Pulse Duration (sec)

Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

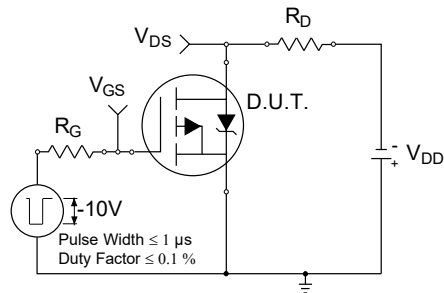


Figure 12a: Switching Time Test Circuit

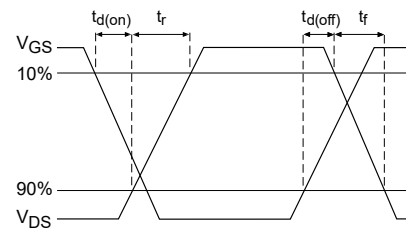


Figure 12b: Switching Time Waveforms

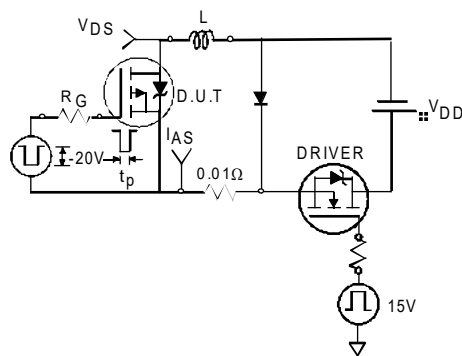


Figure 13a: Unclamped Inductive Test Circuit

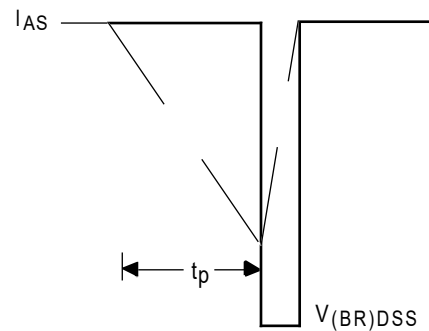


Figure 13b: Unclamped Inductive Waveforms

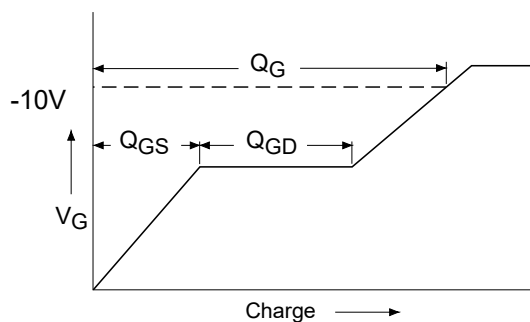


Figure 14a: Basic Gate Charge Waveform

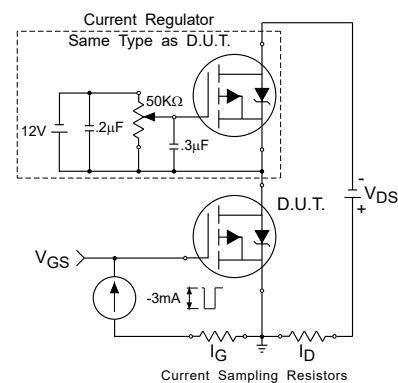
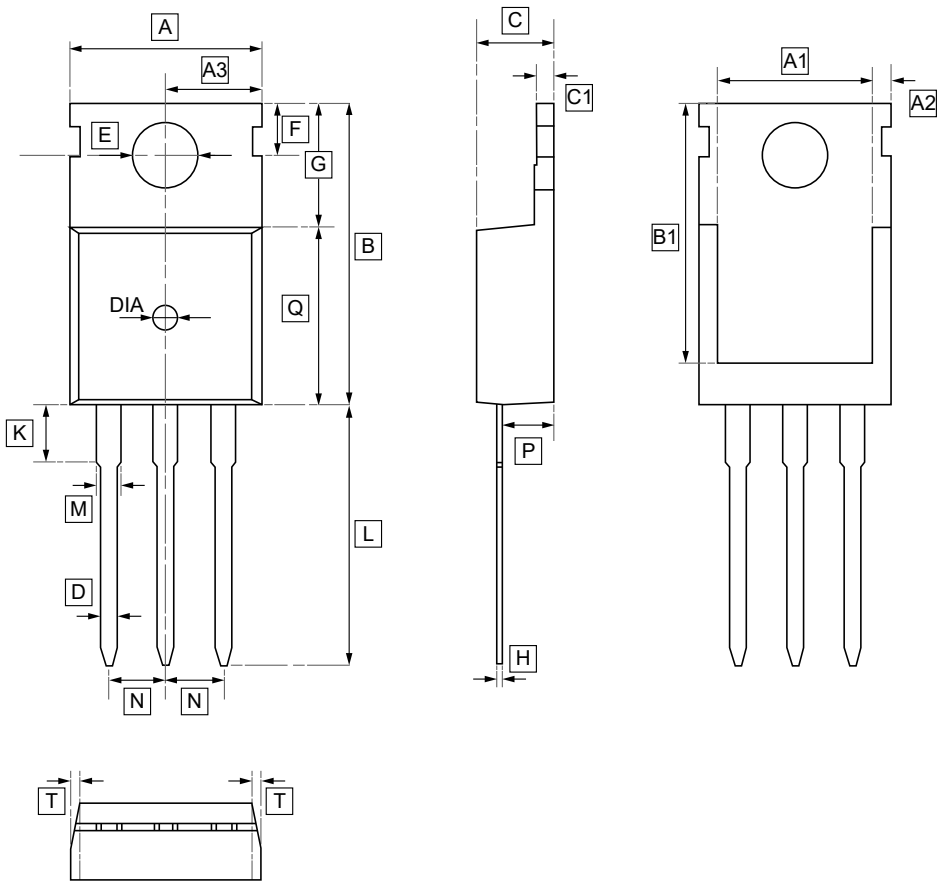


Figure 14b: Gate Charge Test Circuit



8.TO-220 Package Outline Dimensions



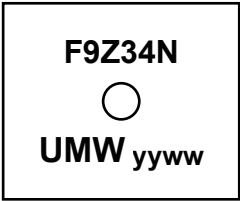
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	B	B1	C	C1	D	E	F	G
Min	9.7	8.44	1.05	4.8	15.4	12.9	4.28	1.1	0.6	3.4	2.65	5.2
Max	10.3	8.84	1.25	5.2	16.2	13.5	4.68	1.5	1.0	3.8	3.25	5.8

Symbol	H	K	L	L1	M	N	P	Q	T	DIA
Min	0.4	2.9	12.8	2.7	1.15	2.49	2.1	8.7	W:0.35	⌀1.5
Max	0.6	3.3	13.6	3.3	1.35	2.59	2.7	9.3		(deep 0.2)



9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW IRF9Z34N	TO-220	1000	Tube and box



10.Disclaimer

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